

(10) **Patent No.:** US 9,218,960 B2
(45) **Date of Patent:** Dec. 22, 2015

- 21/0217* (2013.01); *H01L 21/02129* (2013.01);
H01L 21/02164 (2013.01); *H01L 21/78*
 (2013.01); *H01L 23/29* (2013.01); *H01L*
23/3192 (2013.01); *H01L 23/562* (2013.01);
H01L 29/0603 (2013.01); *H01L 2924/0002*
 (2013.01)

- (58) **Field of Classification Search**
CPC H01L 21/02359; H01L 21/02164;
H01L 21/0217; H01L 21/0214; H01L
21/02129
USPC 438/703; 257/368, 341, 642, 643, 401
See application file for complete search history.

- (56)
- References Cited**

- U.S. PATENT DOCUMENTS

- | | | | | |
|--------------|------|---------|-------------------|---------|
| 8,299,611 | B2 * | 10/2012 | Arvin et al. | 257/738 |
| 2002/0100962 | A1 | 8/2002 | Joshi | |
| 2003/0166341 | A1 * | 9/2003 | Aizawa | 438/694 |

- (Continued)

- FOREIGN PATENT DOCUMENTS

- | | | | |
|----|-----------|----|--------|
| DE | 10343084 | B4 | 7/2006 |
| JP | H06275713 | A | 9/1994 |

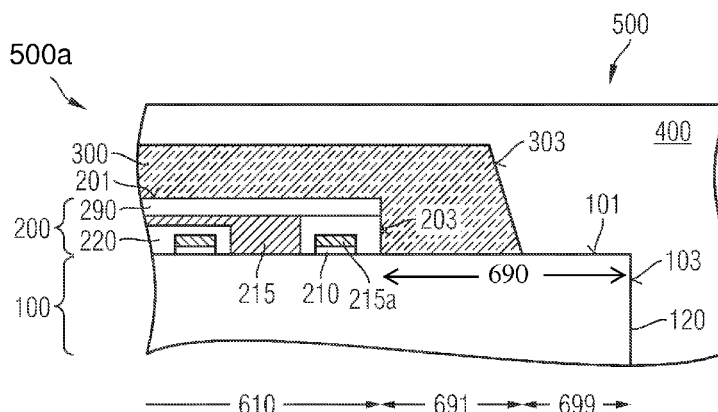
- Primary Examiner* — Bilkis Jahan

- (74) *Attorney, Agent, or Firm* — Murphy, Bilak & Homiller,
PLLC

- (57) **ABSTRACT**

- A method of manufacturing a semiconductor device includes providing a layered structure having a hard dielectric layer containing a first dielectric material having a Young's modulus greater than 10 GPa in a central portion of a main surface of a main body comprising a single crystalline semiconductor body, and providing a dielectric stress relief layer containing a second dielectric material having a lower Young's modulus than the first dielectric material, the stress relief layer covering the layered structure and extending beyond an outer edge of the layered structure.

- ### 7 Claims, 7 Drawing Sheets



US 9,218,960 B2

Page 2

(56)

References Cited

U.S. PATENT DOCUMENTS

2008/0237226	A1	10/2008	Yong	
2008/0237726	A1 *	10/2008	Dyer	257/369
2011/0095392	A1 *	4/2011	Wahl et al.	257/503
2004/0219724	A1 *	11/2004	Park et al.	438/197
2008/0006910	A1	1/2008	Miyata et al.	

* cited by examiner

FIG 2B

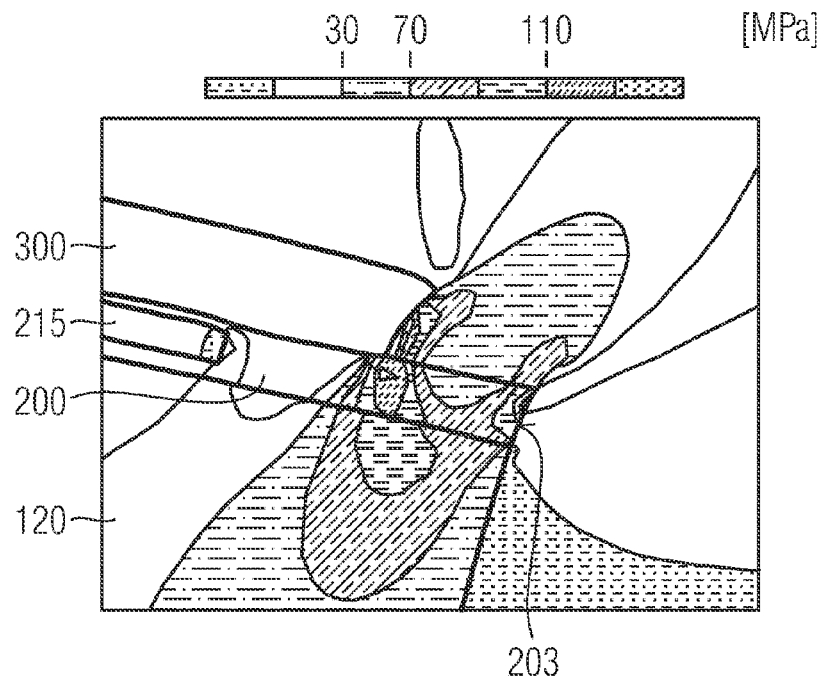


FIG 2C

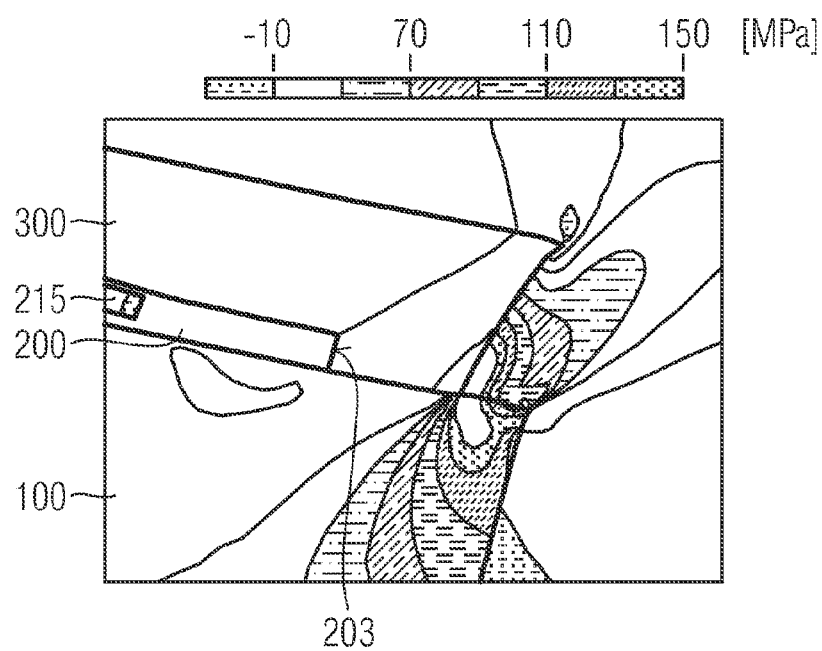


FIG 2D

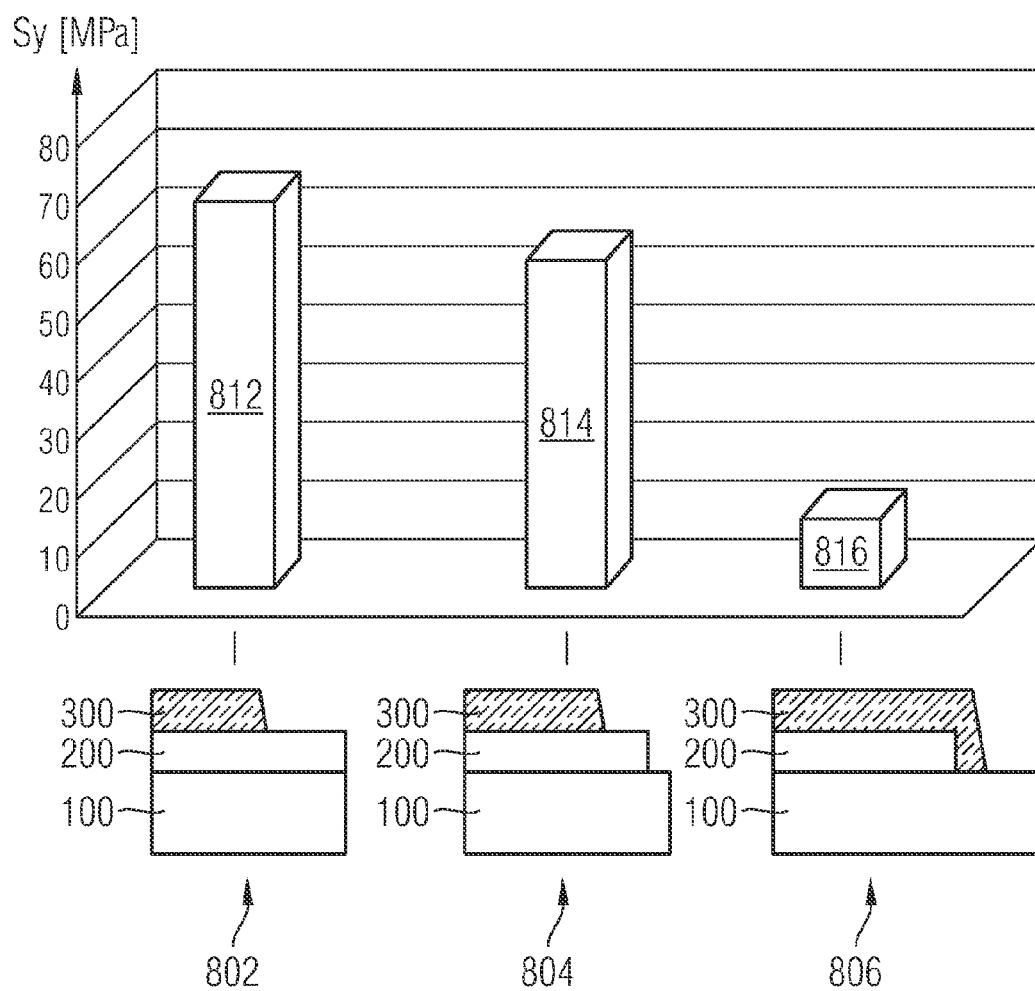


FIG 3A

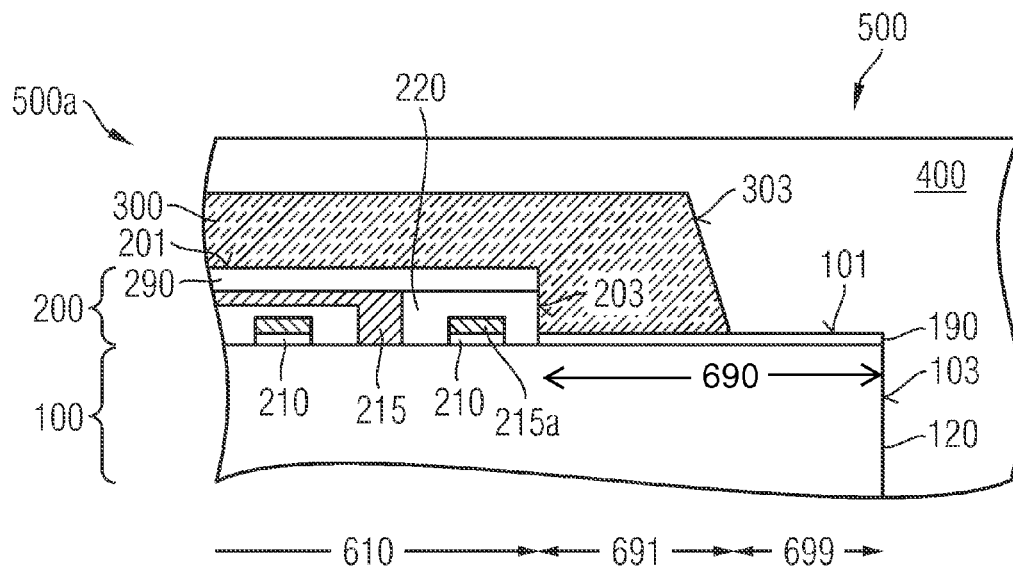


FIG 3B

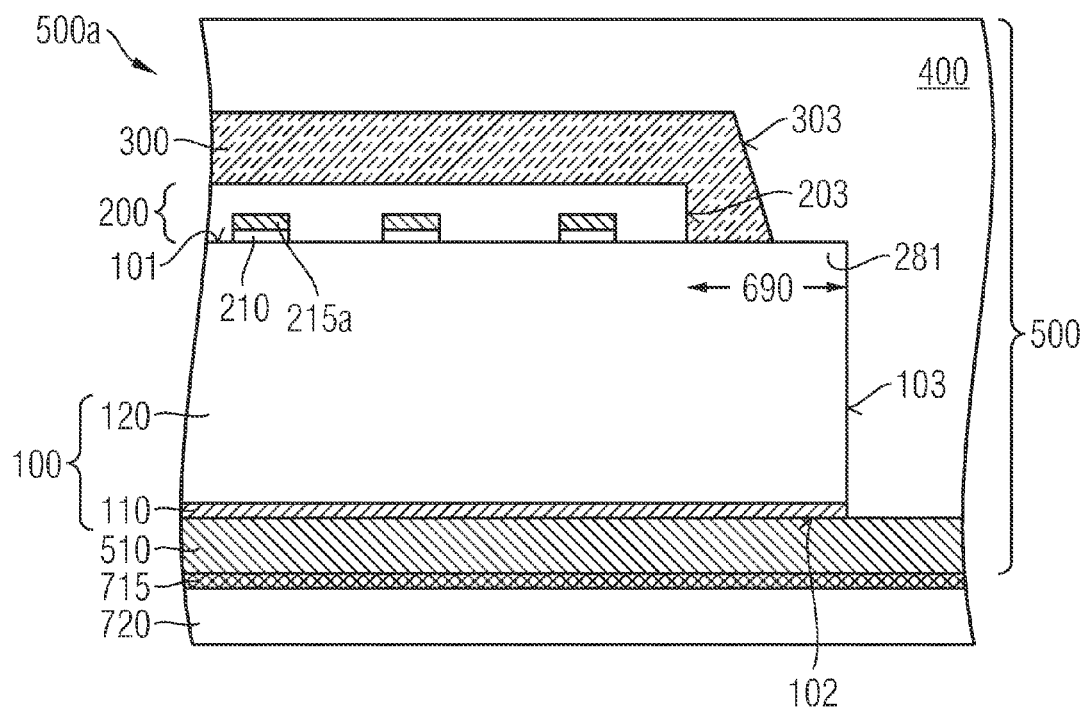


FIG 4A

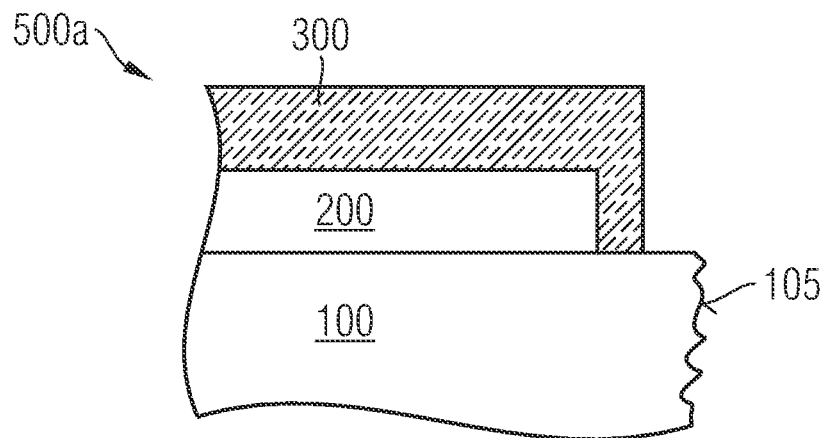


FIG 4B

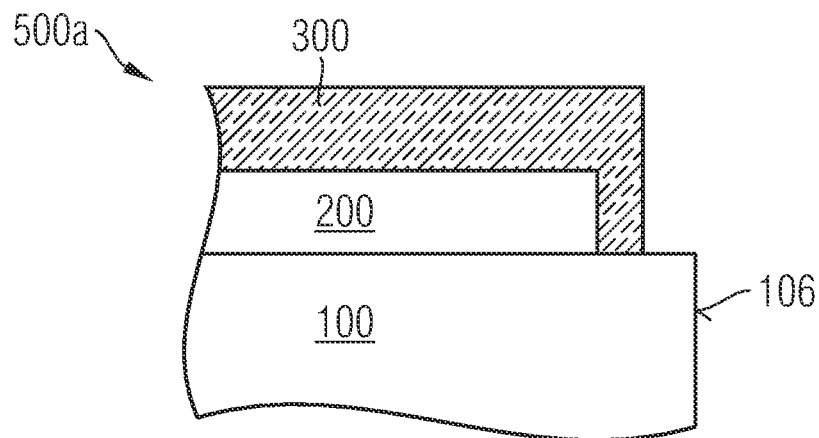


FIG 4C

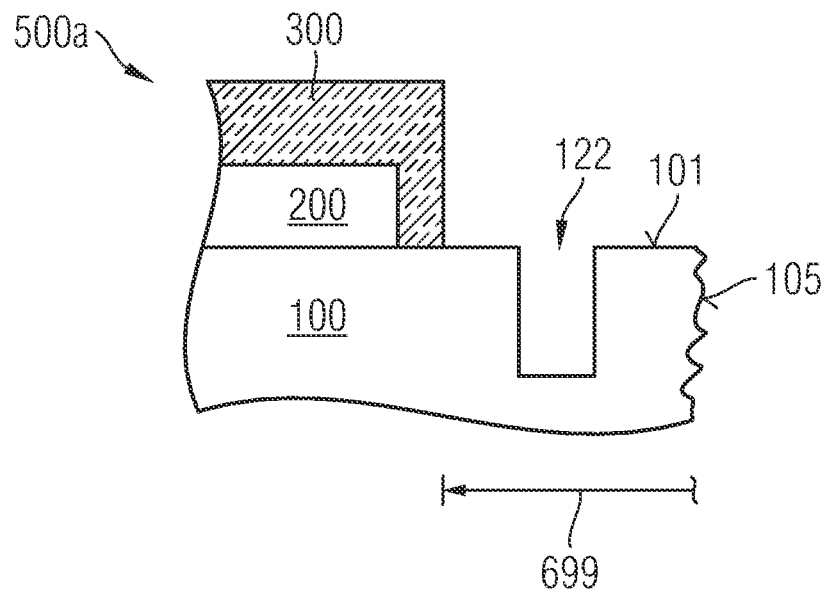
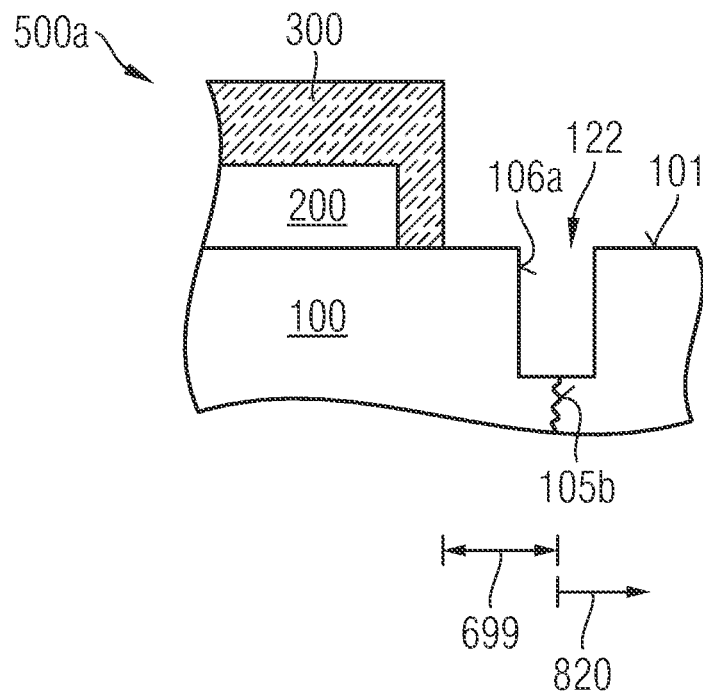
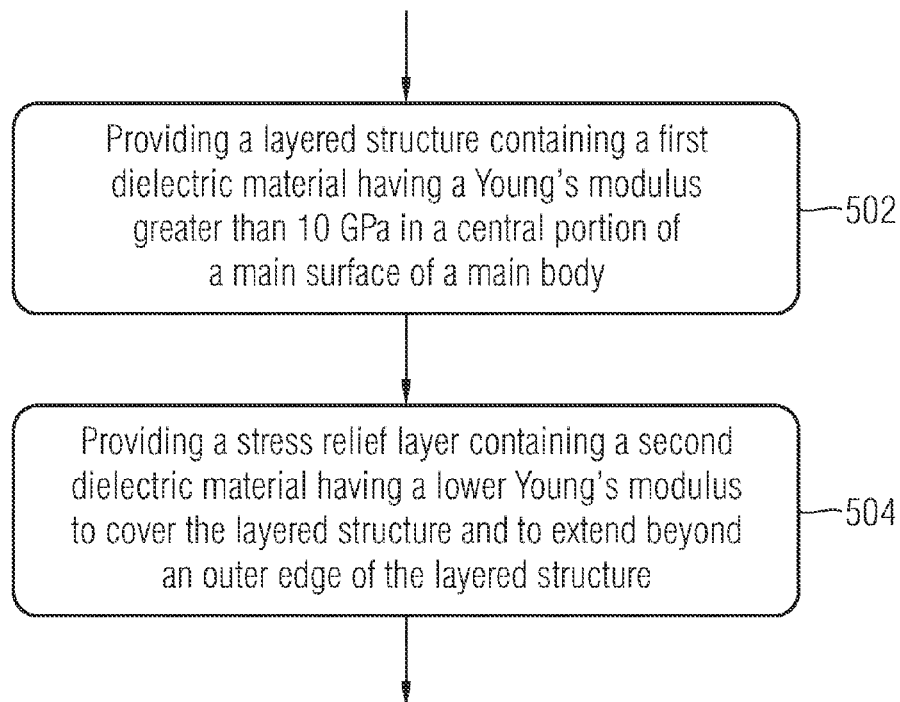


FIG 4D





1

METHOD OF MANUFACTURING A SEMICONDUCTOR DEVICE INCLUDING A STRESS RELIEF LAYER

PRIORITY CLAIM

This application is a Divisional of U.S. application Ser. No. 13/571,462, filed on 10 Aug. 2012, the content of said application incorporated herein by reference in its entirety.

BACKGROUND

Passivation layers, for example plasma oxide or plasma nitride layers, protect semiconductor dies against corrosion and mechanical damages. Typically a passivation layer is provided after patterning the topmost metallization or wiring layer. A stress relief layer, e.g., a polyimide layer, improves adhesion between the passivation layer and a molding mass encapsulating the semiconductor die. It is desirable to improve the reliability of semiconductor devices.

SUMMARY

According to an embodiment, a semiconductor device includes a main body that includes a single crystalline semiconductor body. A layered structure directly adjoins a central portion of a main surface of the main body and includes a hard dielectric layer provided from a first dielectric material with Young's modulus greater than 10 gigapascals (GPa). A dielectric stress relief layer directly adjoins the layered structure opposite to the main body and extends beyond an outer edge of the layered structure.

According to an embodiment providing a method of manufacturing a semiconductor device, a layered structure is provided in a central portion of a main surface of a main body that includes a single crystalline semiconductor body. The layered structure includes a hard dielectric layer that contains a first dielectric material with a Young's modulus greater than 10 GPa. A dielectric stress relief layer is provided to cover the layered structure and to extend beyond an outer edge of the layered structure.

Those skilled in the art will recognize additional features and advantages upon reading the following detailed description and on viewing the accompanying drawings.

BRIEF DESCRIPTION OF THE DRAWINGS

The accompanying drawings are included to provide a further understanding of the invention and are incorporated in and constitute a part of this specification. The drawings illustrate the embodiments of the present invention and together with the description serve to explain principles of the invention. Other embodiments of the invention and intended advantages will be readily appreciated as they become better understood by reference to the following detailed description.

FIG. 1 is a schematic cross-sectional view of an edge portion of a semiconductor device in accordance with an embodiment providing a stress relief layer with a portion in contact with a single crystalline semiconductor surface.

FIG. 2A is a schematic cross-sectional view of an electronic assembly according to a comparative example.

FIG. 2B is a schematic diagram illustrating a stress gradient along a device edge according to a comparative example.

FIG. 2C is a schematic diagram illustrating a stress gradient along a device edge in accordance with an embodiment.

FIG. 2D is a schematic diagram visualizing the stress reduction achieved by the embodiments.

2

FIG. 3A is a schematic cross-sectional view of an edge portion of a semiconductor device in accordance with an embodiment providing a stress relief layer with a portion in contact with a non-single crystalline surface.

FIG. 3B is a schematic cross-sectional view of a portion of an electronic assembly in accordance with another embodiment.

FIG. 4A is a schematic cross-sectional view of an edge portion of a semiconductor device according to an embodiment providing singulation of semiconductor devices by sawing from a main surface.

FIG. 4B is a schematic cross-sectional view of an edge portion of a semiconductor device according to an embodiment providing singulation of semiconductor dies by etching from a main surface.

FIG. 4C is a schematic cross-sectional view of an edge portion of a semiconductor device according to an embodiment providing singulation of semiconductor dies by sawing outside a circumferential trench structure.

FIG. 4D is a schematic cross-sectional view of an edge portion of a semiconductor device according to an embodiment providing singulation of semiconductor dies by sawing through circumferential trench structures.

FIG. 4E is a schematic cross-sectional view of a kerf portion of a semiconductor substrate in accordance with an embodiment providing partially filled circumferential trench structures.

FIG. 5 is a simplified flow chart illustrating a method of manufacturing a semiconductor device according to a further embodiment.

DETAILED DESCRIPTION

In the following detailed description, reference is made to the accompanying drawings, which form a part hereof and in which are shown by way of illustration specific embodiments in which the invention may be practiced. It is to be understood that other embodiments may be utilized and structural or logical changes may be made without departing from the scope of the present invention. For example, features illustrated or described for one embodiment can be used on or in conjunction with other embodiments to yield yet a further embodiment. It is intended that the present invention includes such modifications and variations. The examples are described using specific language which should not be construed as limiting the scope of the appending claims. The drawings are not scaled and are for illustrative purposes only. For clarity, the same elements have been designated by corresponding references in the different drawings if not stated otherwise.

The terms "having", "containing", "including", "comprising" and the like are open and the terms indicate the presence of stated structures, elements or features but not preclude additional elements or features. The articles "a", "an" and "the" are intended to include the plural as well as the singular, unless the context clearly indicates otherwise.

FIG. 1 shows an edge portion 690 of a semiconductor die 500a of a semiconductor device 500 with a main body 100 having a flat main surface 101. The main body 100 includes a single crystalline semiconductor body 120 formed from a single crystalline semiconductor material, for example silicon Si, silicon carbide SiC, germanium Ge, silicon germanium SiGe, gallium nitride GaN or gallium arsenide GaAs. The semiconductor body 120 may include doped layers and zones of both conductivity types as well as further conductive and insulating structures.

In a cell area of the main body **100** corresponding to a central portion **610** of the main surface **101**, elements of one or more diode or field effect transistor (FET) structures may be provided that define the function of the semiconductor device **500**. The semiconductor device **500** may be, for example, a semiconductor diode, an IGFET (insulated gate field effect transistor), for example an MOSFET (metal oxide semiconductor field effect transistor) in the usual meaning including FETs with metal and with non-metal gate electrodes, or an IGBT (insulated gate bipolar transistor). Each diode or field effect transistor structure may include a plurality of cells arranged in one or more cell arrays. The semiconductor device **500** may be a super junction device.

The illustrated embodiment provides gate electrodes **215a** provided at a distance to the main body **100**. According to another embodiment, the semiconductor body **120** may include gate trench structures extending from the main surface **101** into the semiconductor body **120**, the gate trench structures including gate electrode structures, gate dielectrics, field electrodes and insulator structures insulating the gate electrode structures and the field electrodes from each other and the semiconductor material embedding the gate trench structures.

A layered structure **200** directly adjoins the central portion **610** of the main surface **101**. The layered structure **200** includes one or more dielectric layers and may include conductive structures **215**, for example gate electrodes **215a**, provided on the main surface **101** and/or in one or more wiring planes at a distance to the main surface **101**. According to the illustrated embodiment, the layered structure **200** may include, at least in sections, a gate dielectric **210** formed below the gate electrodes **215a**. The gate dielectric **210** may be a thermally grown semiconductor oxide, such as a silicon oxide in the case of a silicon single crystalline semiconductor body **120**. One or more interlayer dielectrics **220** insulate neighboring conductive structures **215**, **215a** within the same wiring plane and may separate neighboring wiring planes.

The layered structure **200** may include a main dielectric layer provided from BSG (boron silicate glass), PSG (phosphorus silicate glass) or BPSG (boron phosphorus silicate glass). A thin silicon oxide layer deposited by using, for example, TEOS (tetraethylorthosilane) as precursor material, may be arranged between the main dielectric layer and the main surface **101**.

The layered structure **200** includes at least one hard dielectric layer **290** provided from a first dielectric material having a Young's modulus greater than 10 GPa. According to an embodiment, the first dielectric material is an inorganic dielectric. For example, the hard dielectric layer **290** is a passivation layer, such as a silicon oxide layer, a silicon nitride layer, or a silicon oxynitride layer provided by chemical vapor deposition and having a thickness of at least 0.2 and at most 2.0 micrometer.

A stress relief layer **300** directly adjoins a layer surface **201** of the layered structure **200**, opposite to the main body **100**, and extends beyond the outer edge of the layered structure **200**. The stress relief layer **300** consists of or contains a second dielectric material that has a Young's modulus at most half of the Young's modulus of the first dielectric material forming the first dielectric layer **290**. A first portion of the stress relief layer **300** adjoining the layer surface **201** and a second portion adjoining an outer surface **203** of the layered structure **200** tilted to the layer surface **201** may be of the same second dielectric material or may be of different second dielectric materials.

According to an embodiment, Young's modulus of the second dielectric material(s) is at most a tenth of Young's

modulus of the first dielectric material. Each second dielectric material may be a polymer with Young's modulus being less than 10 GPa. By way of example, each second dielectric material is or contains polyimide, benzocyclobutene, polynorbornene, polystyrene, polycarbonate, parylene, epoxy resin or a mixture therefrom. In one particular embodiment, for example, the first dielectric material is a silicon oxide with a Young's modulus of about 80 GPa and the second dielectric material is polyimide with a Young's modulus of about 3.2 GPa.

The stress relief layer **300** covers the outer surface **203** of the layered structure **200**, wherein the outer surface **203** is tilted to the layer surface **201**. According to an embodiment, the outer surface **203** is perpendicular to the layer surface **201**. The stress relief layer **300** covers an inner edge portion **691** of the main surface **101** surrounding the central portion **610** and forming part of edge portion **690** between the central portion **610** and an outer edge **103** of the main body **100**. The distance between an outer edge **303** of the stress relief layer **300** and the outer surface **203** of the layered structure **200** may be at least 3 micrometer, and in a particular embodiment may be at least 5 micrometer. The distance between the outer edge **303** of the stress relief layer **300** and the outer edge **103** of the main body **100** may be at least 5 micrometer, and in a particular embodiment may be at least 10 micrometer. The semiconductor device **500** may further include a molding mass **400** encapsulating the semiconductor die **500a**. The material of the molding mass **400** may be a ceramic or a plastic.

Drawing back the outer surface **203** of the layered structure **200** from the outer edge **103** of the main body **100**, i.e., providing the layered structure **200** at a distance to the outer edge **103**, allows for forming the outer surface **203** using an etch process. In contrast to a sawing process, etch processes do not leave cracks in the etched sidewalls, such that the outer surface **203** is typically without cracks. The outer surface **203** of the layered structure **200** is not adversely affected by sawing a semiconductor substrate to obtain singulated semiconductor dies **500a**, wherein in the semiconductor substrate a plurality of identical semiconductor dies **500a** are formed. Extending the stress relief layer **300** beyond the edge of the layered structure **200** protects the outer surface **203** against thermo-mechanic stress induced by subsequent rapid thermal processing steps, such as soldering.

FIG. 2A illustrates a destructive mechanism induced by initially non-critical sawing features. A layered structure **200** is provided on a main surface **101** of a main body **100** including a semiconductor body **120**. The layered structure **200** includes conductive structures **215**, including, inter alia, at least one gate electrode **215a** and a gate dielectric **210** separating the gate electrode **215a** and the single crystalline semiconductor body **120**. The layered structure **200** covers the main surface **101** completely such that an outer surface **203** of the layered structure **200** is flush with an outer edge **103** of the main body **100**. A stress relief layer **300** is deposited on at least a portion of the layered structure **200**. A semiconductor die **500a** including the main body **100**, the layered structure **200** and the stress relief layer **300** may be obtained by sawing a semiconductor substrate, providing a plurality of identical semiconductor dies **500a**.

The sawing may induce small cracks **281** along the outer surface **203** of the layered structure **200**. The small cracks **281** typically do not exceed a length of 10 to 15 micrometers and do not necessarily adversely affect the functionality of the semiconductor die **500a**, such that the singulated semiconductor die **500a** may initially pass all tests for functionality.

The semiconductor die **500a** may be mounted on a heat slug **510** directly contacting a backside surface **102** of the

main body **100** opposite to the main surface **101**, wherein the main body **100** may or may not include a backside metallization **110** along the backside surface **102**. The heat slug **510** may be made of copper Cu or an alloy including copper, by way of example. A molding mass **400** encapsulates the semiconductor die **500a** and may expose at least portions of the heat slug **510**. The molding mass **400** is a plastic or a ceramic material.

A semiconductor device **500** provided by the encapsulated semiconductor die **500a** is mounted on a PCB (printed circuit board) **720** by soldering, resulting in a solder layer **715** between the heat slug **510** and the PCB **720**. During soldering at temperatures of, for example, 260 degree Celsius, the molding mass **400** expands, inducing a tensile stress along the outer surface **203** of the layered structure **200**. The induced tensile stress is a function of the solder temperature, especially as the solder temperature ramps up.

FIG. 2B shows that for the arrangement of FIG. 2A the effective tensile stress may amount to 100 megapascals (MPa) at a fast heat up of 200 degree Celsius per second. The tensile stress may pull apart portions of the layered structure **200** on both sides of an initially non-critical crack **281** such that the crack propagates up to several 100 micrometer in a direction parallel to the main surface **101** into the layered structure **200**, as indicated by the dotted line in FIG. 2A. The propagating crack may enter the semiconductor body **120** for several tens of micrometers, and may exit the semiconductor body **120**, for example, below a gate dielectric **210**. Propagating into the gate dielectric, the crack may damage the gate dielectric **210**. As a result, the semiconductor device **500** is defective.

Drawing the outer surface **203** of the layered structure **200** back from the outer edge **103** of the semiconductor die **500a**, along which the semiconductor die **500a** is sawn, reduces initial damages of the layered structure **200**.

Extending the stress relief layer **300** beyond the outer surface **203** of the layered structure **200** significantly reduces the stress that is effective on the outer surface **203**, as shown in FIG. 2C. As a result of both measures, the reliability of the semiconductor device **500** is significantly improved.

FIG. 2D shows the tensile stress S_y in MPa at the edge of a layered structure **200** embodied by a silicon oxide layer with a thickness of 2 micrometer. In a conventional arrangement **802**, the tensile stress S_y is greater than 60 MPa, as shown in column **812**. Drawing back the outer edge of the silicon oxide layer **200a** by 20 micrometer, as for arrangement **804**, reduces the maximum tensile stress by about 10 GPa, as shown by column **814**. Drawing back the outer edge of the silicon oxide layer **200a** by 30 micrometer and extending a stress relief layer **300** embodied by a polyimide layer beyond the edge of the silicon oxide layer **200a** by 10 micrometer, as for arrangement **806**, approximately reduces the maximum stress by a factor 10, as shown by column **816**.

FIG. 3A refers to an embodiment that differs from the embodiment of FIG. 1 in that the main body **100** includes an additional layer **190** between the main surface **101** and the semiconductor body **120**. The additional layer **190** may be formed exclusively in the inner edge portion **691**, exclusively in the outer edge portion **699** or in the complete edge portion **690**. The additional layer **190** may be a sub-layer of the layered structure **200**. According to an embodiment, the additional layer **190** may be a thin dielectric layer with a thickness of less than 200 nanometer. For example, the additional layer **190** may be a thin silicon nitride layer or a thin silicon oxide layer, such as a native oxide or a terminal oxide.

The electronic assembly FIG. 3B differs from the electronic assembly of FIG. 2A in that the layered structure **200** is

absent in an edge portion **690** of the main surface **101** and in that the stress relief layer **300** extends over the outer edge **203** of the layered structure **200**. Since damages induced by sawing are avoided in the layered structures **200** and since the stress relief layer **300** effectively protects the outer edge **203** from tensile stress during soldering the semiconductor device **500** onto the PCB **720**, fewer cracks occur in the layered structure **200** and propagation of the cracks is suppressed. The electronic assembly **700** shows fewer failures during operation.

The semiconductor devices **500** of FIGS. 1, 3A and 3B may be manufactured on a semiconductor substrate, such as a silicon wafer, with a plurality of device regions that are arranged in a matrix and separated by a kerf grid (kerf frame). The kerf frame may include PCM (process control monitoring) features, test circuits and/or lithographic marks. In each device region, a semiconductor die **500a** is formed by providing, in a central portion of each of the device regions, a layered structure that includes the hard dielectric layer and by providing, in each device region, a stress relief layer at a distance to the kerf frame. In each device region, the stress relief layer covers the layered structure and extends beyond an outer edge of the layered structure.

According to an embodiment, the semiconductor substrate is sawn along the kerf frame, for singulating the semiconductor dies. As shown in FIG. 4A, the resulting rough edge surface **105** of the main body **100**, including the semiconductor body **120**, has a surface roughness greater than 0.1 micrometer.

According to another embodiment, an etch or laser cut process singulates the semiconductor dies **500a** from the semiconductor substrate. The etch and laser cut processes leave a smooth edge surface **106** with significantly less surface roughness, e.g., lower than 0.1 micrometer, as indicated in FIG. 4B.

PCM features, test circuits and lithographic marks may be at least partly removed by a lift-off process using HF or a plasma-enhanced etch process for completely etching through the semiconductor substrate, or by a saving process.

According to another embodiment, an example of which is illustrated in FIG. 4B, the semiconductor die **500a** includes a circumferential trench **122** formed completely in the outer edge portion **699** or in parts in the outer edge portion **699** and a kerf frame **820**. The circumferential trench **122** may extend from the main surface **101** into the main body **100**. The depth of the circumferential trench **122** may be at least 0.1 and at most 60 micrometer. The depth and width of the circumferential trenches **122** may vary. Trenches with wide openings may be completely or partially filled, with conformally deposited layers, for example. According to an embodiment, the center of the circumferential trenches **122** is a void or space. The circumferential trenches **122** stop cracks from propagating from sawing defects at the edge surface **105**, **106** into the main body **100**.

As shown in FIG. 4C, the semiconductor substrate may be sawn outside the circumferential trenches **122**, leaving a rough edge surface **105** between the main surface **101** and the opposing backside surface.

According to another embodiment sawing is performed over the whole width of the kerf frame and cuts both neighboring trenches, respectively. The trenches may be cut in a central, void section such that the trench sidewalls remain sound and untouched.

As shown in FIG. 4D, a first portion **106a** of the edge surface resulting from the trench structure **122** is smooth and a second portion **105b** resulting from sawing shows a surface roughness greater than 0.1 micrometer. An edge surface **105**,

7

106 of the main body **100** perpendicular to the main surface **101** provides a first portion between the main surface **101** and a step distance given by the trench bottom as well as a second portion between the step distance and a backside surface opposing the main surface **101**. The trench structure **122** may extend from the main surface **101** or from the opposing backside surface into the main body **100**. In each case, in a narrower one of the first and second portions corresponding to the trench structure **122**, the roughness is at most 0.1 micrometer and in a wider one of the first and second portions outside the trench structures **122** the roughness is greater than 0.1 micrometer.

An outer surface without initial damage does not induce cracks. The sawing area may have a width of 40 to 100 micrometer, and the width of the trenches may range from 5 to 20 micrometers, by way of example. The process may be combined with IC-technologies providing trenches for other reasons, for example smart transistor technologies combining power transistor technology with logic circuits on the same semiconductor die **500a**.

FIG. 4E shows a semiconductor substrate **500b** with a kerf frame **820a**, **820b** separating two device regions **830**. Each device region **830** provides a semiconductor die **500a**. Each semiconductor die **500a** includes a central portion **610** with a layered structure **200** formed on a main body **100**. A stress relief layer **300** extends over edges of the layered structure **200** into edge portions **690** surrounding the central portions **610**, respectively. In the edge portions **690**, circumferential trenches **122** extend from a main surface **101** into the respective main body **100** and surround the central portions **610**. A conformal oxide layer **124** and a conformal polysilicon layer **126** may line the sidewalls and bottoms of the circumferential trenches **122** and may leave a void **129** in the center of the circumferential trenches **122**. According to an embodiment, the kerf frame **820a** is a part of or the complete portion of the semiconductor substrate **500b** between two neighboring circumferential trenches **122**. According to another embodiment, the kerf frame **820b** includes the inner sidewalls of the circumferential trenches **122** oriented to the neighboring semiconductor die **500a**. The kerf frame **820a**, **820b** may have a width of about 50 to 60 micrometer and the circumferential trenches **122** may have a width of about 5 to 20 micrometer.

According to FIG. 5 a method of manufacturing a semiconductor device includes providing a layered structure in a central portion of a main surface of a main body that includes a single crystalline semiconductor body (**502**). The layered structure includes a hard dielectric layer that contains a first dielectric material with a Young's modulus greater than 10 GPa. A stress relief layer with a lower Young's modulus is provided to cover the layered structure and to extend beyond an outer edge of the layered structure (**504**). The stress relief layer may contain a second dielectric material with a Young's modulus at most half of Young's modulus of the first dielectric material.

According to an embodiment, the stress relief layer may be provided to cover at least an inner edge portion directly adjoining the central portion of the main surface. Providing the layered structure may include depositing the hard dielectric layer containing the first dielectric material and removing the hard dielectric layer in the edge portion. This may be done, for example, by a masked etch process. Other than a sawing process, plasma etch processes do not leave cracks in

8

the etched sidewalls. Providing the stress relief layer may include depositing an unpatterned stress relief layer and removing a portion of the unpatterned stress relief layer from the outer edge portion. The first dielectric material may be silicon oxide, silicon nitride, silicon oxynitride, undoped silicate glass, boron silicate glass, phosphorus silicate glass or boron phosphorus silicate glass, by way of example. Examples for the second dielectric material are polyimide, benzocyclobutene, polynorbornene, polystyrene, polycarbonate, parylene, and epoxy resin.

Although specific embodiments have been illustrated and described herein, it will be appreciated by those of ordinary skill in the art that a variety of alternate and/or equivalent implementations may be substituted for the specific embodiments shown and described without departing from the scope of the present invention. This application is intended to cover any adaptations or variations of the specific embodiments discussed herein. Therefore, it is intended that this invention be limited only by the claims and the equivalents thereof.

What is claimed is:

1. A method of manufacturing a semiconductor device, the method comprising:

providing a layered structure comprising a hard dielectric layer containing a first dielectric material having a Young's modulus greater than 10 GPa on a central portion of a main surface of a main body comprising a single crystalline semiconductor body, the layered structure being absent in an edge portion of the main surface between the central portion and an outer edge of the main body, the outer edge connecting the main surface and a backside surface opposite to the main surface; and providing a dielectric stress relief layer containing a second dielectric material having a lower Young's modulus than the first dielectric material, the stress relief layer covering the layered structure and extending beyond an outer edge of the layered structure.

2. The method according to claim 1, wherein the second dielectric material has a Young's modulus at most half of the Young's modulus of the first dielectric material.

3. The method according to claim 1, wherein the dielectric stress relief layer is provided to cover at least an inner edge portion directly adjoining the central portion of the main surface.

4. The method according to claim 1, wherein providing the layered structure comprises depositing the first dielectric material and removing the first dielectric material in an edge portion by an etch process.

5. The method according to claim 1, wherein providing the stress relief layer comprises depositing an unpatterned stress relief layer and removing a portion of the unpatterned stress relief layer from the outer edge.

6. The method according to claim 1, wherein the first dielectric material is selected from a group comprising silicon oxide, silicon nitride, silicon oxynitride, undoped silicate glass, boron silicate glass, phosphorus silicate glass and boron phosphorus silicate glass.

7. The method according to claim 1, wherein the second dielectric material is selected from a group comprising polyimide, benzocyclobutene, polynorbornene, polystyrene, polycarbonate, parylene, and epoxy resin.

* * * * *